SILICON (Si) POWER MOSFET A CEB60N10



CEB60N10

100V ▲ 20mΩ ▲ 57A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO263 (D2PAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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RoHS

REACH

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	100V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _c = 25°C	I _D	57A
Pulsed Drain Current Note 1	I _{DM}	228A
Maximum Power Dissipation at T _c = 25°C	PD	200W
Power Dissipation Derating above 25°C	ΔP _D	1.3W/°C
Single Pulsed Avalanche Energy Note 4	E _{AS}	560mJ
Single Pulsed Avalanche Current Note 4	I _{AS}	40A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.75°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{th_ja}	62.5°C/W

APPLICATIONS

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

PIN DESCRIPTION

Circuit Diagram	Outline - Bottom View	Pin No.	Description
D (1)		1	Drain
G (3)		2	Source
S (2)		3	Gate

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ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	100			V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I _{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}		20	24	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	CISS		2810		рF
Output Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	Coss		440		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		38		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 30A, $R_{\text{G}(\text{ext})}$ = 2.5 Ω	t _{D(ON)}		26	52	ns
Turn-On Rise Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 30A, $R_{\text{G(ext)}}$ = 2.5 Ω	t _R		5	10	ns
Turn-Off Delay Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 30A, $R_{\text{G(ext)}}$ = 2.5 Ω	t _{D(OFF)}		52	104	ns
Turn-Off Fall Time	V_{DD} = 50V, V_{GS} = 10V, I_{D} = 30A, $R_{\text{G(ext)}}$ = 2.5 Ω	t _F		8	16	ns
Total Gate Charge	V_{DD} = 80V, V_{GS} = 10V, I_{D} = 30A	Q _G		64	76	nC
Gate Source Charge	V_{DD} = 80V, V_{GS} = 10V, I_D = 30A	Q _{GS}		15		nC
Gate Drain Charge	V_{DD} = 80V, V_{GS} = 10V, I_D = 30A	\mathbf{Q}_{GD}		24		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		I _S			57	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 57A	V_{SD}			1.3	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: $L = 0.7 \text{mH}, I_{AS} = 40 \text{A}, V_{DD} = 25 \text{V}, R_G = 25 \Omega$, Starting T_J = 25°C

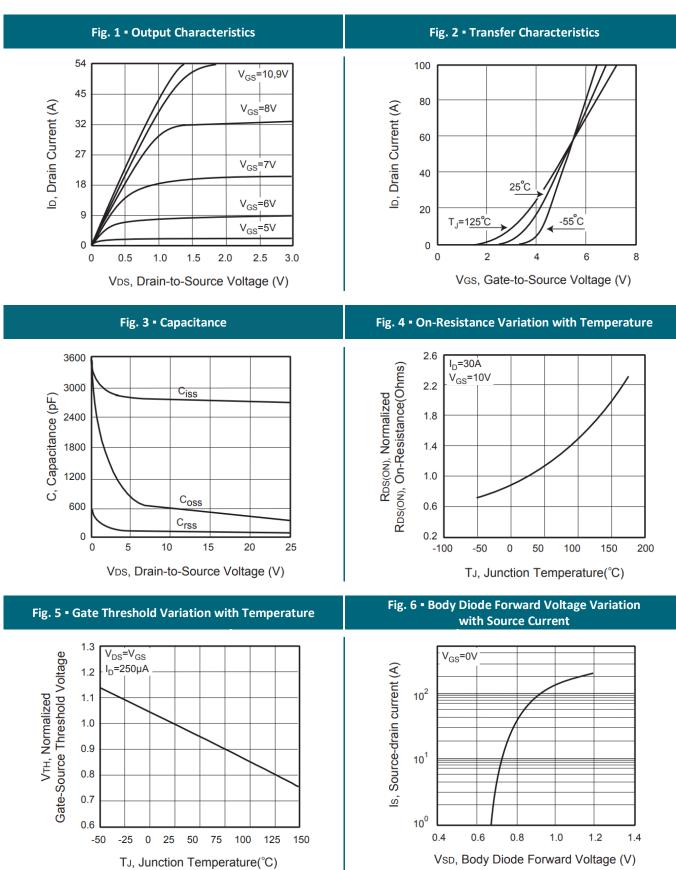


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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



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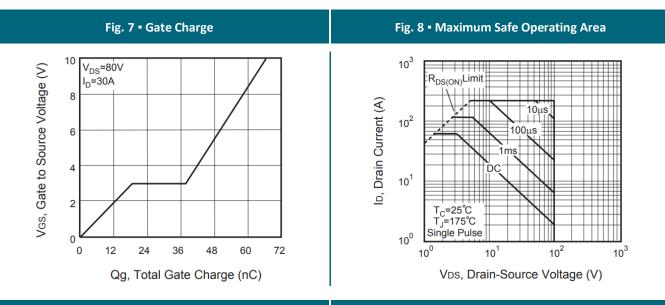
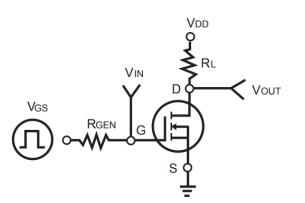


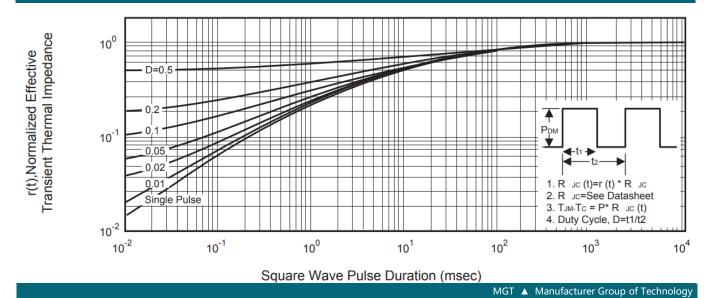
Fig. 9 - Switching Test Circuit



← ton → toff td(off) tr td(on) tf 90% 90% VOUT 10% **INVERTED** 10% 90% 50% 50% Vin 10% PULSE WIDTH

Fig. 10 - Switching Waveforms

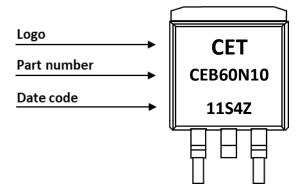
Fig. 11 • Switching Test Circuit



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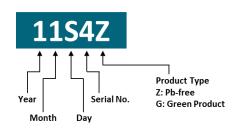






DATE CODE

Example: 11S4Z



Coding list for "Day"

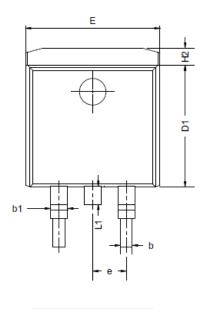
1	2	3	4	5	6	7	8	9	A
01	02	03	04	05	06	07	08	09	10
B	C	D	E	F	G	H	 	J	K
11	12	13	14	15	16	17	18	19	20
L	M	N	0	P	Q	R	S	T	U
21	22	23	24	25	26	27	28	29	30
V 31									

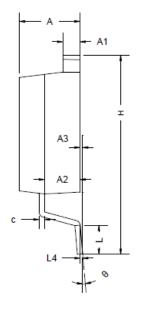
Coding list for "Month"

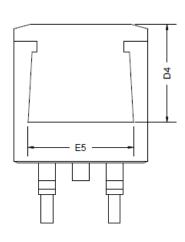
1 an	2 Feb	3 Mar	4 Apr	5 May	6 Jun
7 Iul	8 Aug	9 Sep	A Oct	B Nov	C Dec
	Cod	ling lis	t for "`	Year"	
0		L 2	2 3	3 4	4
202	0 20	21 20	22 20	023 20	24
5	(5 7	7 8	8 9	Э
202	5 20	26 20	27 20	028 20	29



PACKAGE OUTLINE







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	Е	9.86	10.16	10.36
A1	1.22	1.27	1.42	E5	7.06	-	-
A2	2.49	2.69	2.89	е		2.54 BSC	
A3	0.00	0.13	0.25	Н	14.70	15.10	15.50
b	0.70	0.81	0.96	H2	1.07	1.27	1.47
b1	1.17	1.27	1.47	L	2.00	2.30	2.60
с	0.30	0.38	0.53	L1	1.40	1.55	1.70
D1	8.50	8.70	8.90	L4		0.25 BSC	
D4	6.60	-	-	θ	0°	5°	9°

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB60N10	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs

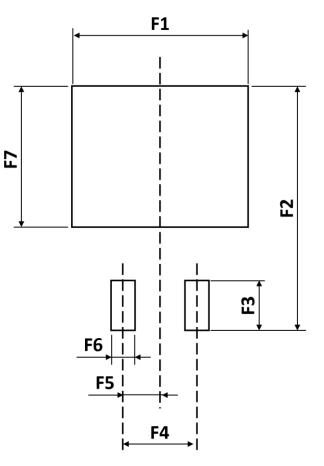
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RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-	F5	-	2.54	-
F2	-	16.90	-	F6	-	1.60	-
F3	-	2.54	-	F7	-	9.75	-
F4	-	5.08	-				

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

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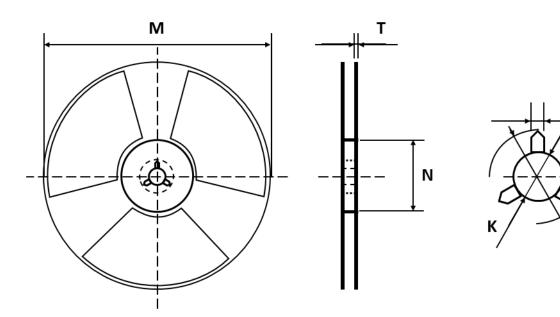


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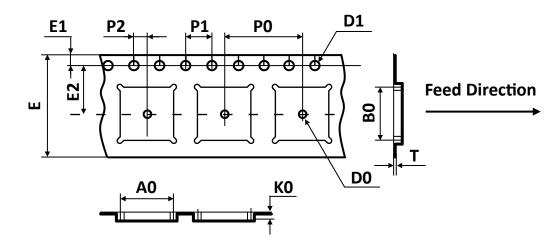


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
	24mm Ø330	Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm		±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS All dimensions in mm



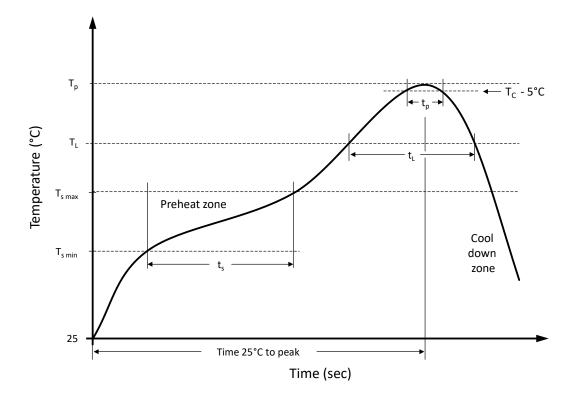
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05







RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	tL	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max. 30 seconds max.	
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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